Features

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Description

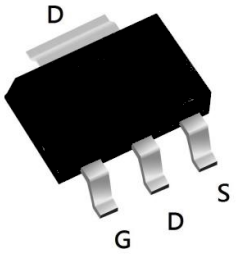
The JHL3002 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

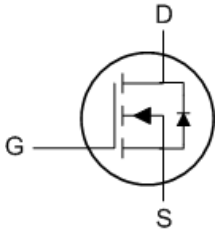
The JHL3002 meet the RoHS and Green Product requirement with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
30V	28mΩ	5.8A

SOT-223 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	5.8	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ 10V[1]	4.7	A
I_{DM}	Pulsed Drain Current[2]	30	A
P_D@T_A=25°C	Total Power Dissipation[3]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	85	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	48	°C/W

Electrical Characteristics (T_J=25 ˚C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25˚C , I_D=1mA	---	0.025	---	V/˚C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=5A	---	24	28	mΩ
		V_{GS}=4.5V , I_D=4A	---	34	40	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.8	---	mV/˚C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25˚C	---	---	1	uA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25˚C	---	---	5	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=5A	---	7	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.5	5	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=5A	---	6	8.4	nC
Q_{gs}	Gate-Source Charge		---	2.5	3.5	
Q_{gd}	Gate-Drain Charge		---	2.1	2.9	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω I_D=5A	---	2.4	4.8	ns
T_r	Rise Time		---	7.8	14	
$T_{d(off)}$	Turn-Off Delay Time		---	22	44	
T_f	Fall Time		---	4	8	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	572	800	pF
C_{oss}	Output Capacitance		---	81	112	
C_{rss}	Reverse Transfer Capacitance		---	65	91	
Diode Characteristics						
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	5.8	A
I_{SM}	Pulsed Source Current[2,4]		---	---	30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25˚C	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=5A , dI/dt=100A/μs , T_J=25˚C	---	19	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.04	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150˚C junction temperature
4.The data is theoretically the same as I_D and I_S , in real applications , should be limited by total power dissipation.

Typical Characteristics

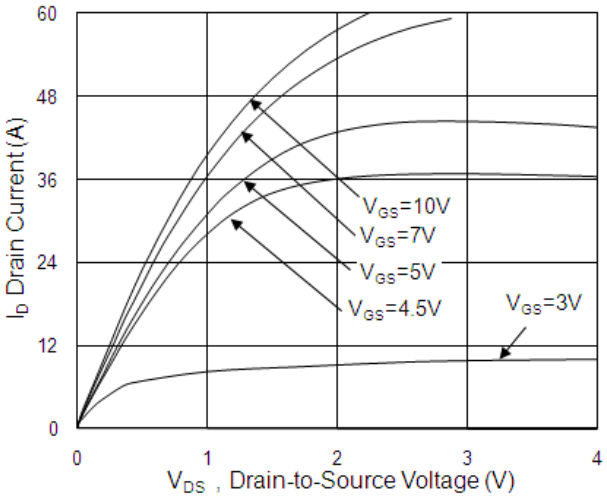


Fig.1 Typical Output Characteristics

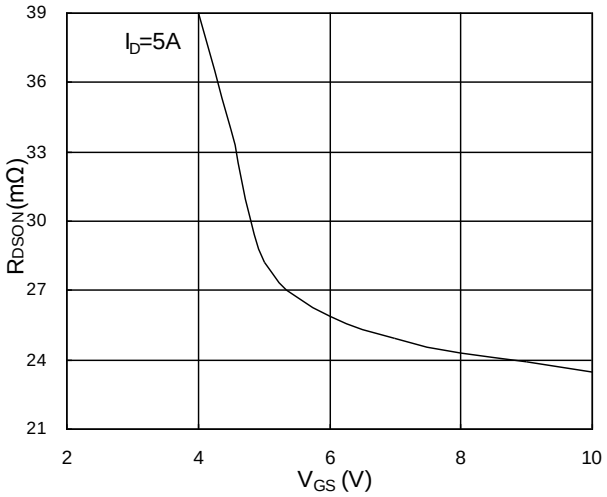


Fig.2 On-Resistance vs. Gate-Source

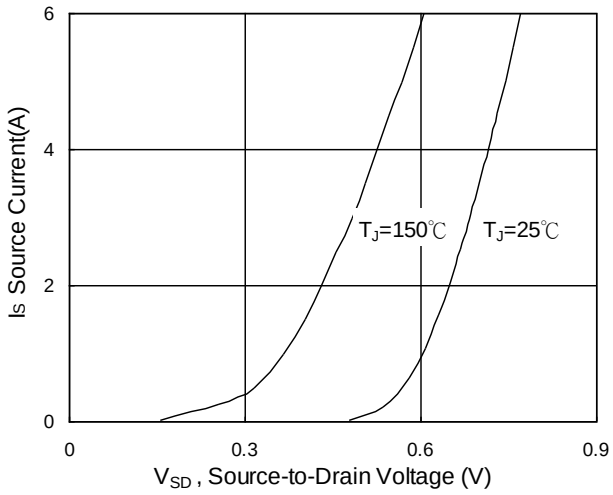


Fig.3 Forward Characteristics of Reverse

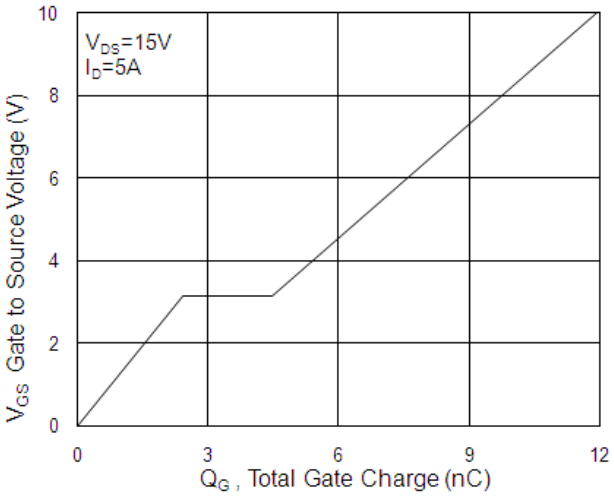


Fig.4 Gate-Charge Characteristics

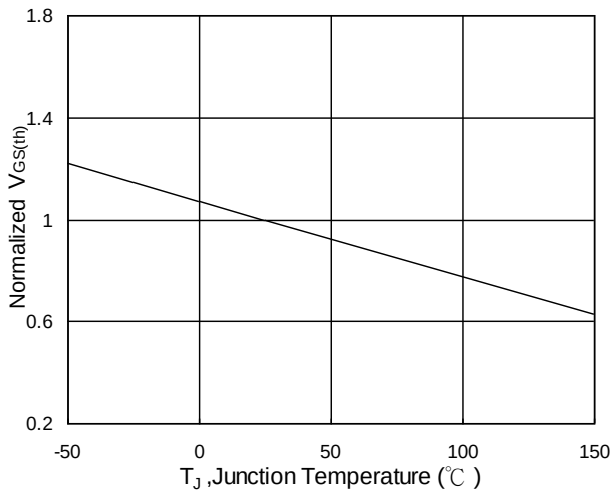


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

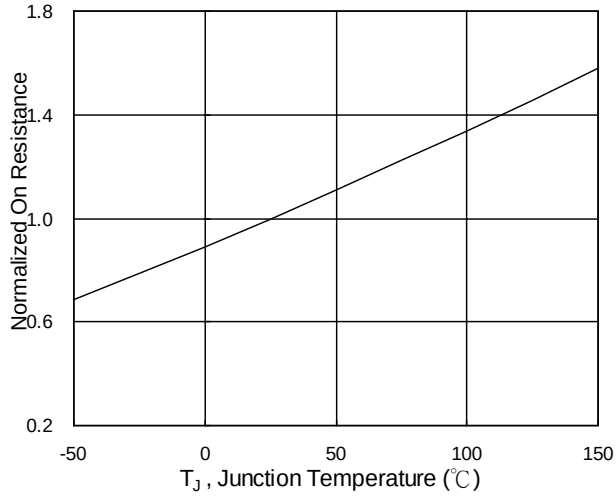


Fig.6 Normalized R_{DSON} vs. T_J

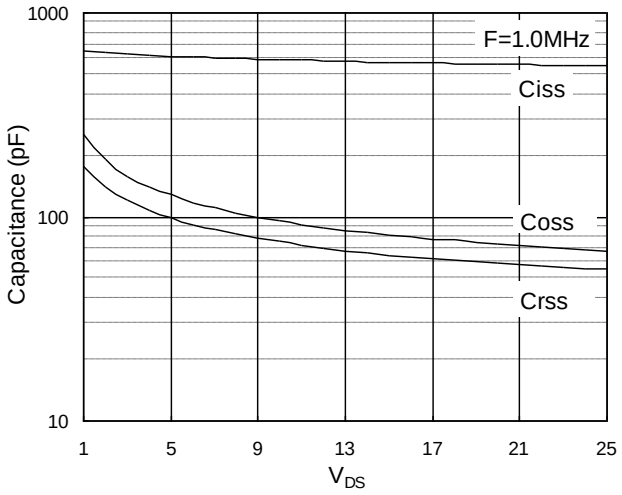


Fig.7 Capacitance

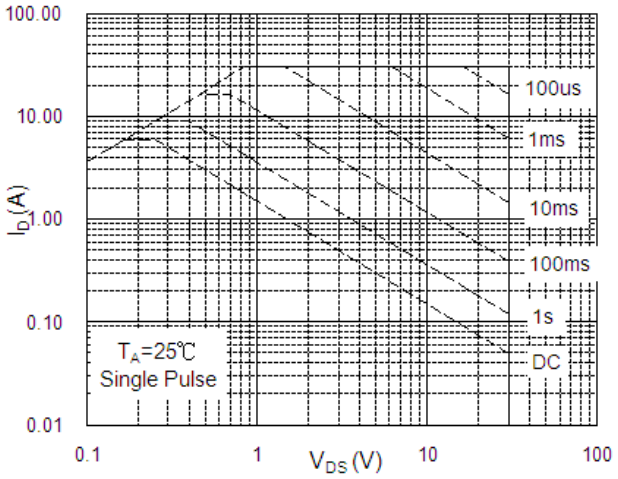


Fig.8 Safe Operating Area

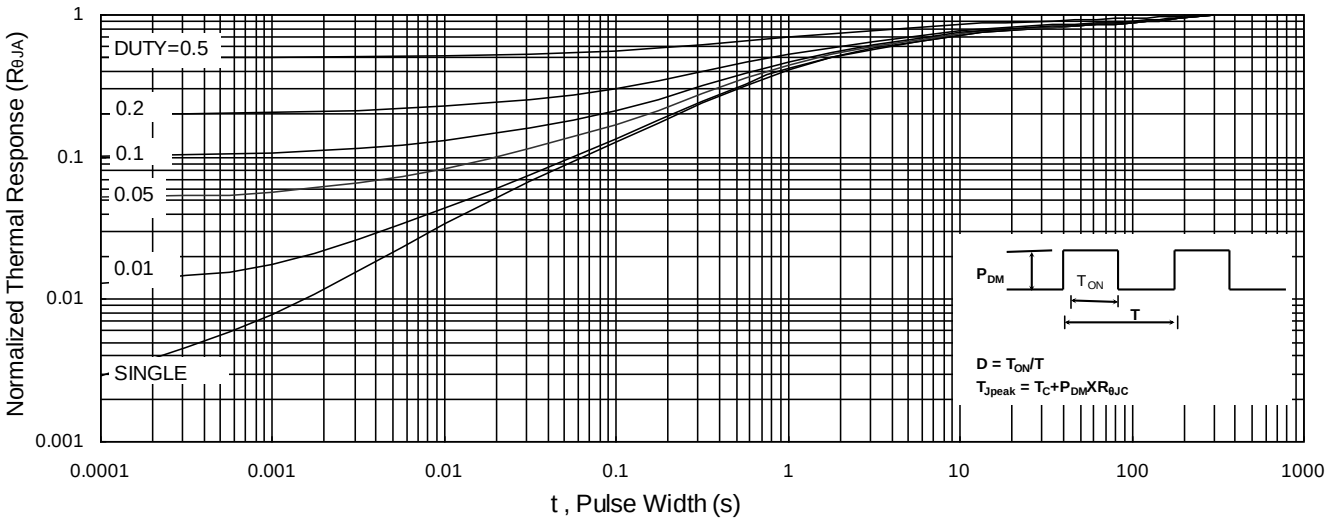


Fig.9 Normalized Maximum Transient Thermal Impedance

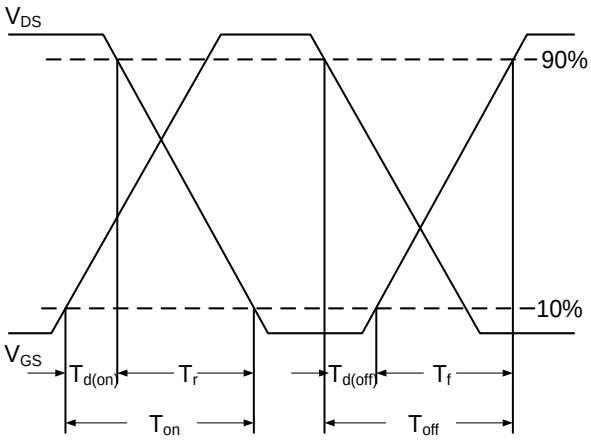


Fig.10 Switching Time Waveform

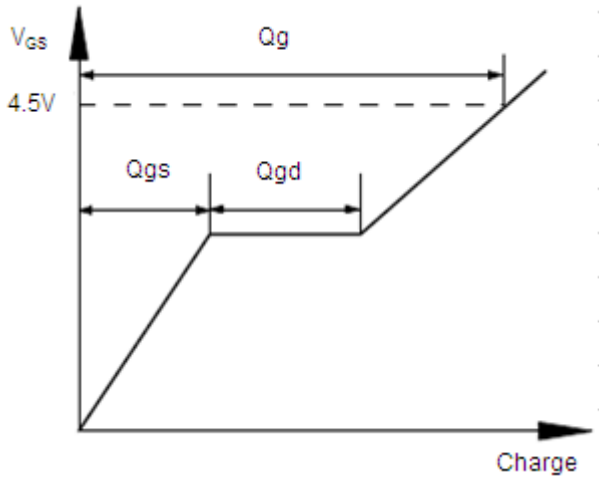
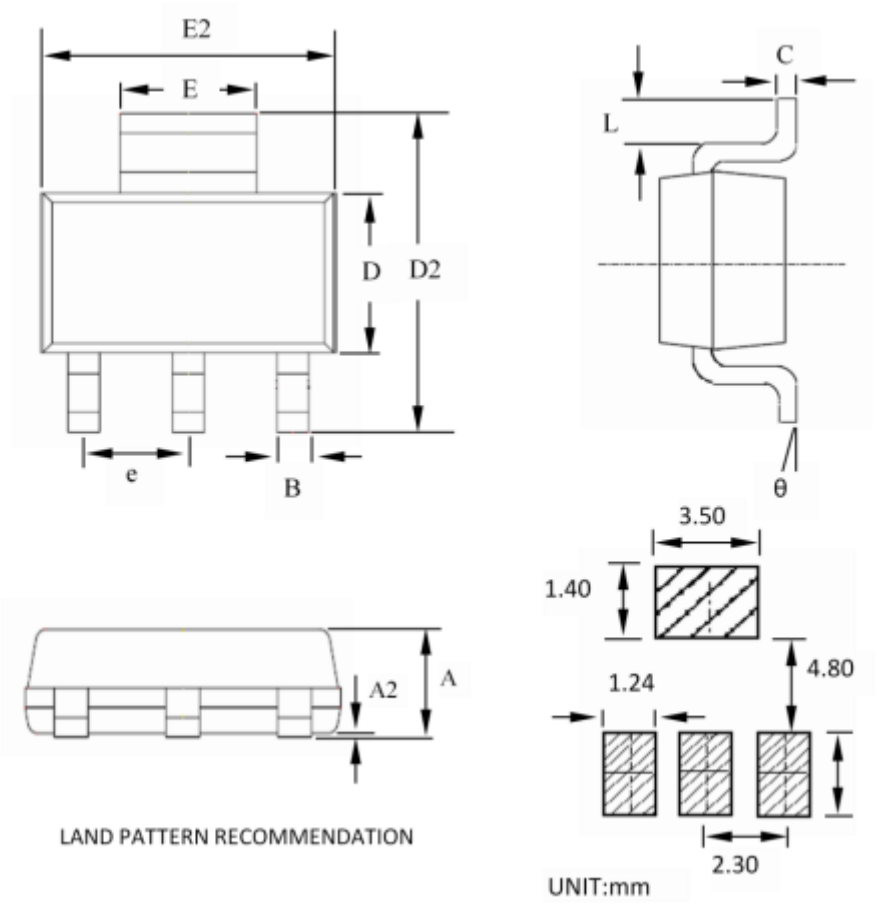


Fig.11 Gate Charge Waveform

SOT-223 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	--	1.80	0.059	--	0.071
A2	0.02	--	0.10	0.001	--	0.004
B	0.60	0.70	0.84	0.024	0.028	0.033
C	0.23	--	0.35	0.009	--	0.014
D	3.30	3.50	3.70	0.130	0.138	0.146
D2	6.70	--	7.30	0.264	--	0.287
E	2.90	3.00	3.10	0.114	0.118	0.122
E2	6.30	6.50	6.70	0.248	0.256	0.264
L	0.75	0.90	1.00	0.030	0.035	0.039
θ	0°	--	10°	0°	--	10°
e	--	2.30	--	--	0.091	--

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